

F	2018-4				
G	2018-10-22				
H	2019-1-09	1			
I	2019-6-13		取消 RDSON@-20V/-10A 的项目		
J	2022-1-10		VGSS=±20V 改为±25V; 特征栏和IGSS中 VGSS=±20V 改为±25V; 极限参数中删除 E 描述。		

/ Descriptions

SOP-8 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

/ Features

$V_{DS} (V) = -30V$

$I_D = -12 A (V_{GS} = \pm 25V)$

$R_{DS(ON)} < 14m\Omega (V_{GS} = -10V)$

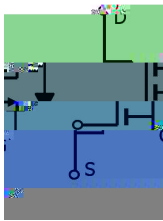
无卤产品。HF Product.

/ Applications

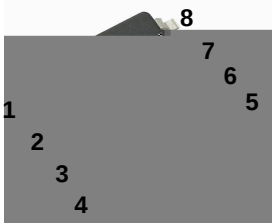
用于电源管理，便携式设备和电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Equivalent Circuit



/ Pinning



PIN 1 : S	PIN 2 : S	PIN 3 : S	PIN 4 : G
PIN 5 : D	PIN 6 : D	PIN 7 : D	PIN 8 : D

/ Marking

见印章说明 See Marking Instructions.

/ Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 25	V
Continuous Drain Current ^A	$I_D (T_a=25^\circ\text{C})$	-12	A
Continuous Drain Current ^A	$I_D (T_a=70^\circ\text{C})$	-10	A
Pulsed Drain Current ^B	I_{DM}	-60	A
Power Dissipation for Single Operation ^A	$P_D (T_a=25^\circ\text{C})$	3	W
Power Dissipation for Single Operation ^A	$P_D (T_a=100^\circ\text{C})$	2.1	W
Maximum Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient ^A	$R_{\theta JA} \quad t \leq 10s$	40	$^\circ\text{C/W}$
Thermal Resistance-Junction to Ambient ^A	$R_{\theta JA}$	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	30	$^\circ\text{C/W}$

Note:

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

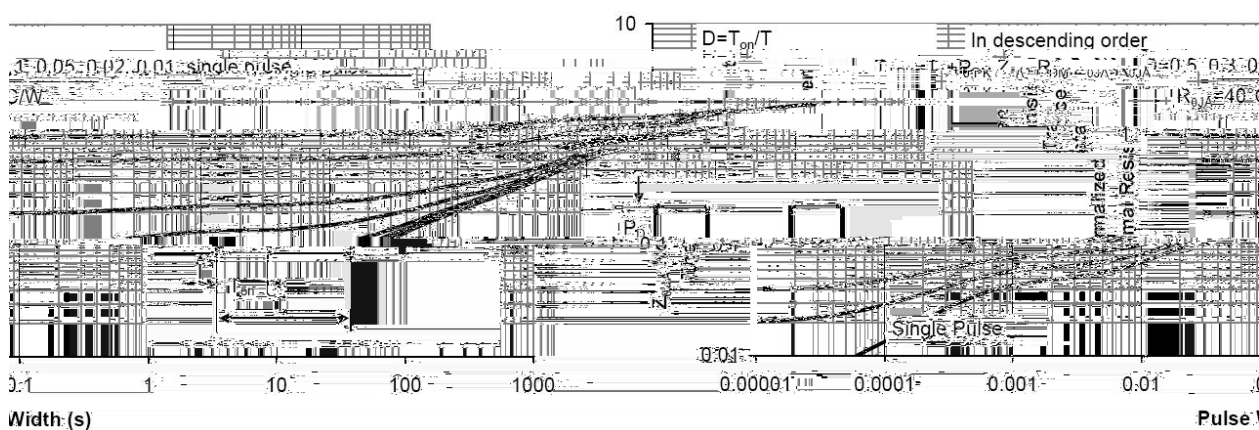
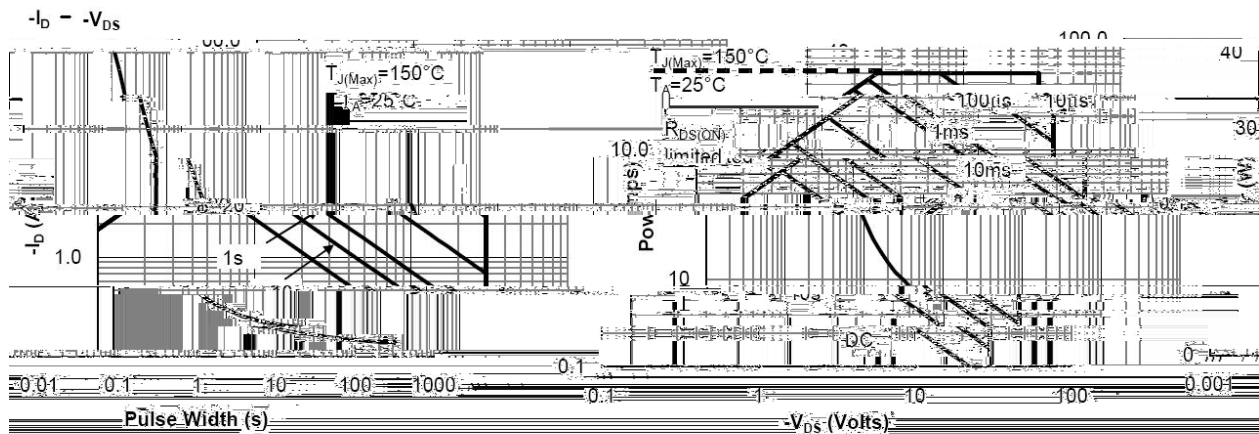
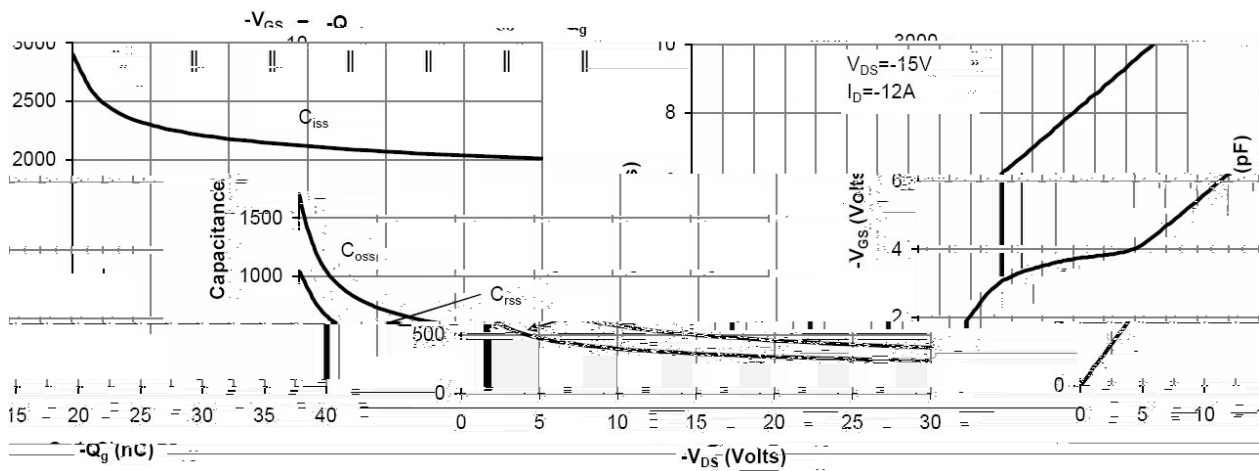
B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

Parameter	Symbol	Test Conditions	Min	Typ	Max
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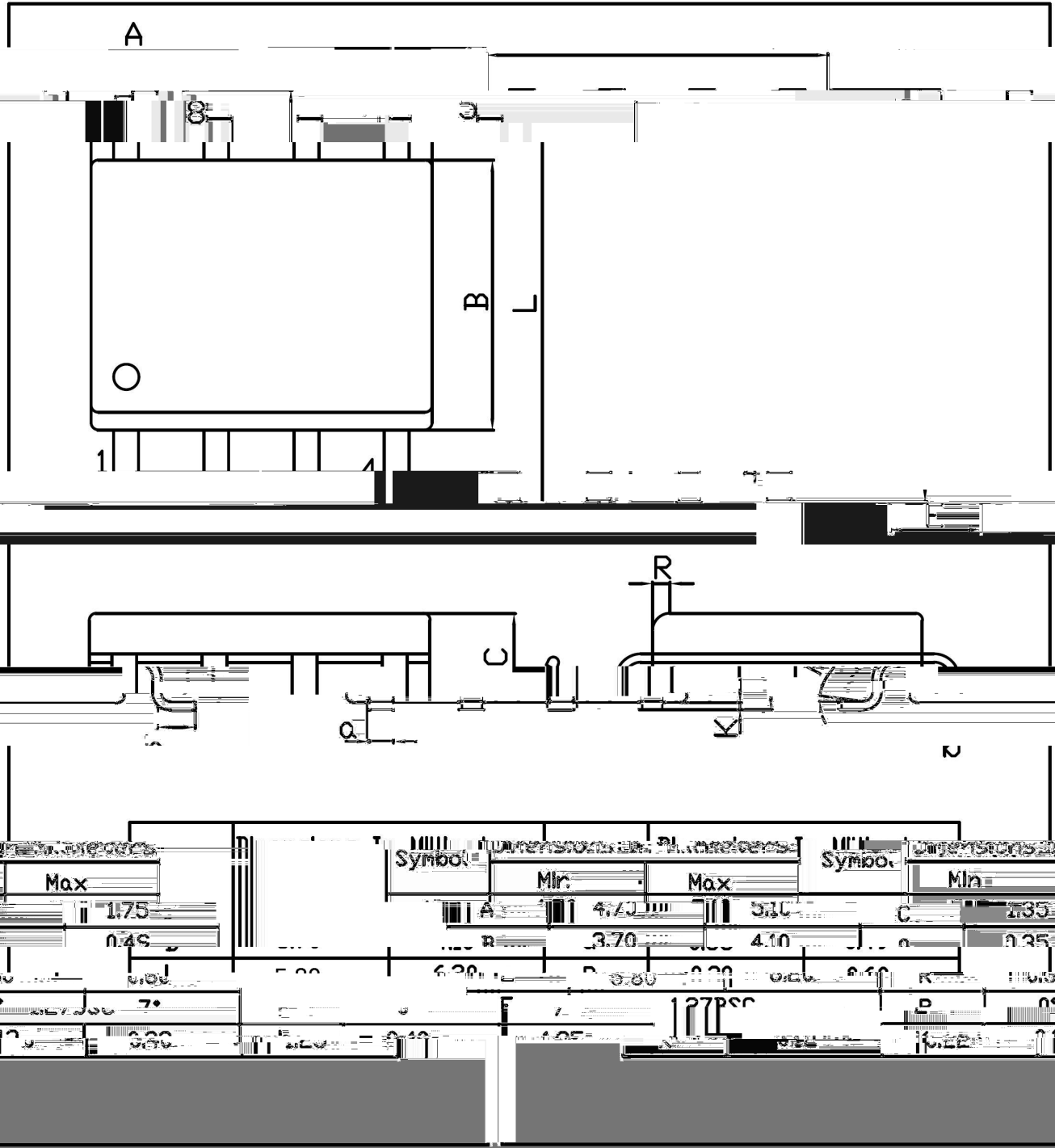
/ Electrical Characteristic Curve



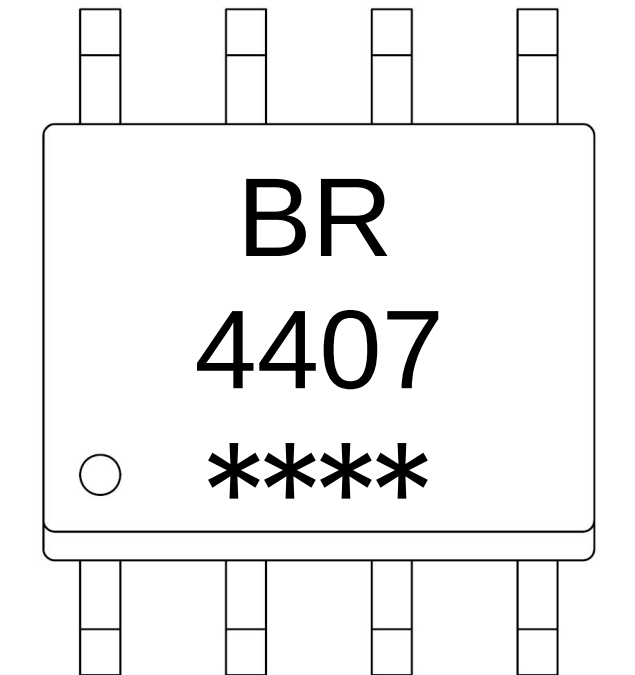
/ Package Dimensions

SOP-8

Unit:mm



/ Marking Instructions



说明：

BR： 为公司代码

4407： 为型号代码

****： 为生产批号代码，随生产批号变化。

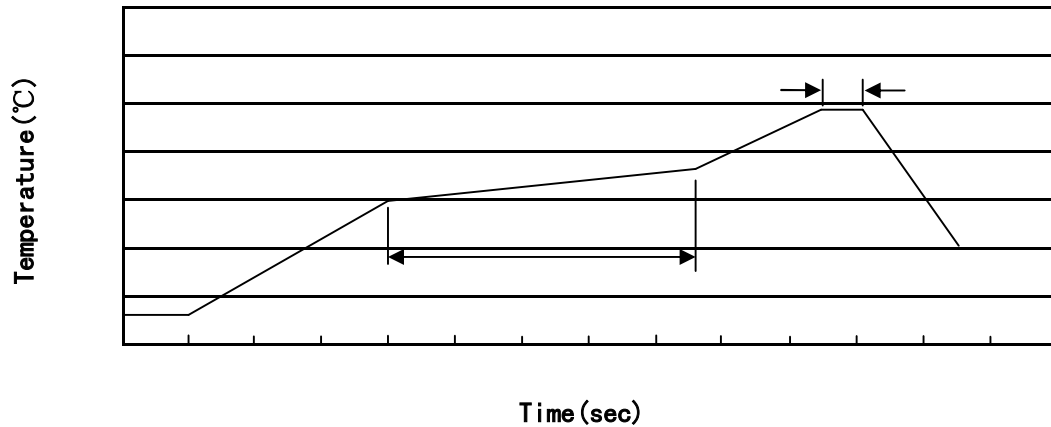
Note:

BR: Company Code.

4407: Product Type

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1. 150 180 60 90sec; 1.Preheating:150~180°C, Time:60~90sec.
2. 245±5 5±0.5sec; 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. 2 10°C/sec. 3. Cooling Speed: 2~10°C/sec.

/ Resistance to Soldering Heat Test Conditions

260±5°C 10±1 sec. Temp.:260±5°C Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

/ Notices